



WANSEMI
万芯半导体

WP30H80KFB

Enhancement Mode N-Channel Power MOSFET

TO-220/NMOS/30V/ ± 20 V/1.5V/180A/2.2m Ω

Rev0.1

30V, 2.2mΩ, 180A, N-Channel MOSFET

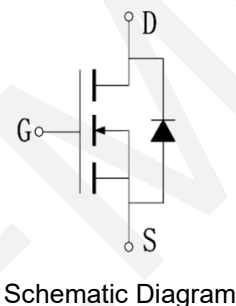
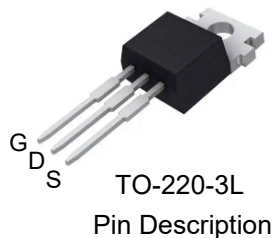
1.Features

- ◆ Advanced Trench Technology
- ◆ Excellent $R_{DS(on)}$ and Low Gate Charge
- ◆ Lead Free

V_{DS}	$R_{DS(on)}$ Typ.	I_D Max.
30V	2.2mΩ @ 10V	180A
	3.3mΩ @ 4.5V	

2.Applications

- ◆ Load Switch
- ◆ PWM Application
- ◆ Power Management



3.Package Marking and Ordering Information

Part no.	Marking	Package	PCS/Tube	PCS/CTN.
WP30H80KFB	WP30H80K	TO-220	50	5,000

4.Absolute Max Ratings at Ta=25°C (Note1)

Parameter	Symbol	Maximum	Units
Drain to Source Voltage	V_{DSS}	30	V
Gate to Source Voltage	V_{GSS}	±20	V
Drain Current (DC)	I_D	180	A
Drain Current (Pulse), $PW \leq 300\mu s$	I_{DP}	720	A
Total Dissipation	P_D	347	W
Avalanche Energy, Single Pulsed	E_{AS}	240	mJ
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-55 to +150	°C

Note 1: Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

5. Thermal Resistance Ratings

Parameter	Symbol	Value	Unit
Junction to Ambient	$R_{\theta JA}$	30	$^{\circ}\text{C/W}$
Junction to case	$R_{\theta JC}$	0.36	$^{\circ}\text{C/W}$

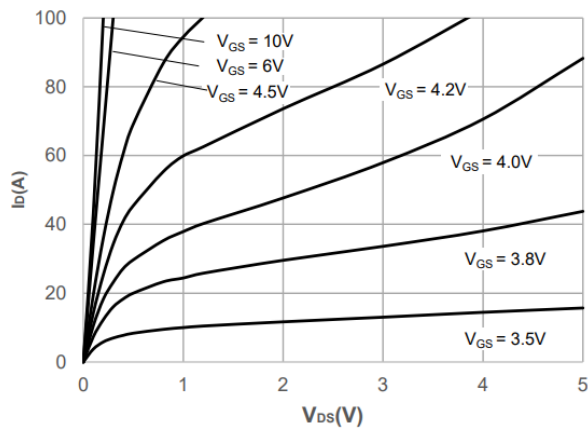
Note 2: When mounted on 1 inch square copper board $t \leq 10\text{sec}$ The value in any given application depends on the user's specific board design.

6. Electrical Characteristics at $T_a=25^{\circ}\text{C}$ (Note 3)

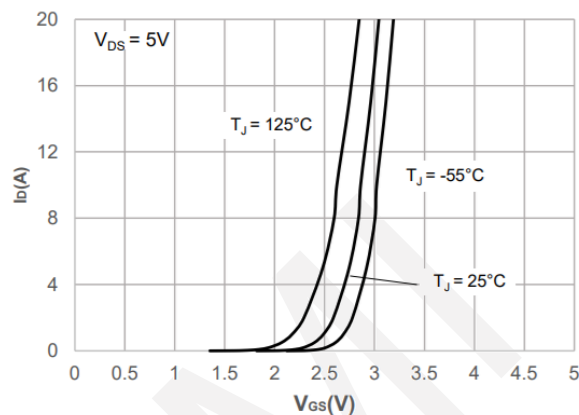
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Drain to Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 250\mu\text{A}$, $V_{GS} = 0\text{V}$	30			V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 30\text{V}$, $V_{GS} = 0\text{V}$			1	μA
Gate to Source Leakage Current	I_{GSS1}	$V_{GS} = \pm 20\text{V}$, $V_{SS} = 0\text{V}$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{DS}=250\mu\text{A}$	1.0	1.5	2.5	V
Static Drain to Source On-State Resistance	$R_{DS(on)}$	$I_D = 20\text{A}$, $V_{GS} = 10\text{V}$	-	2.2	2.8	$\text{m}\Omega$
		$I_D = 10\text{A}$, $V_{GS} = 4.5\text{V}$	-	3.3	4.5	$\text{m}\Omega$
Input Capacitance	C_{iss}	$V_{GS}=0\text{V}$, $V_{DS}=15\text{V}$, Frequency=1.0MHz		3650		pF
Output Capacitance	C_{oss}			494		pF
Reverse Transfer Capacitance	C_{rss}			366		pF
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 15\text{V}$, $I_D=30\text{A}$ $V_{GS} = 10\text{V}$, $R_{GEN} = 3\Omega$,		10		ns
Rise Time	t_r			19		ns
Turn-off Delay Time	$t_{d(off)}$			50		ns
Fall Time	t_f			20		ns
Total Gate Charge	Q_g	$V_{DD}= 30\text{V}$, $V_{GS} = 0 \text{ to } 10\text{V}$, $I_D = 15\text{A}$		67		nC
	Q_{gs}			11		nC
	Q_{gd}			19		nC
Diode Forward Voltage	V_{FSD}	$I_S = 20\text{A}$, $V_{GS} = 0$			1.2	V

Note 3: Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

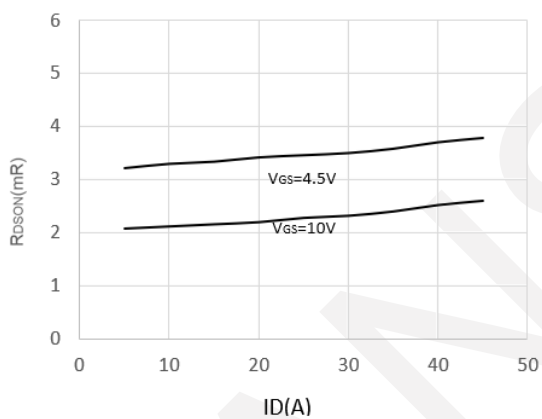
7. Typical electrical and thermal characteristics



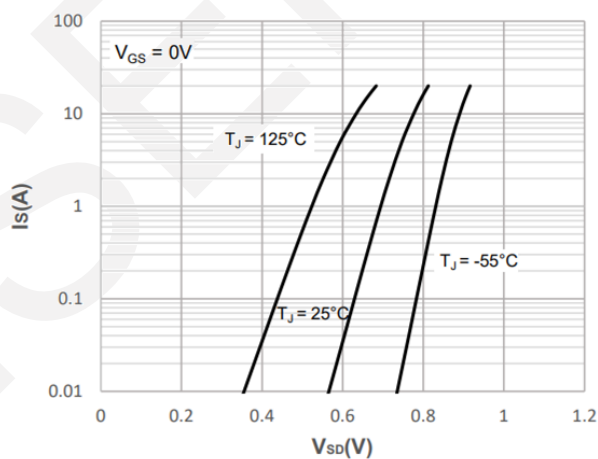
Output Characteristics



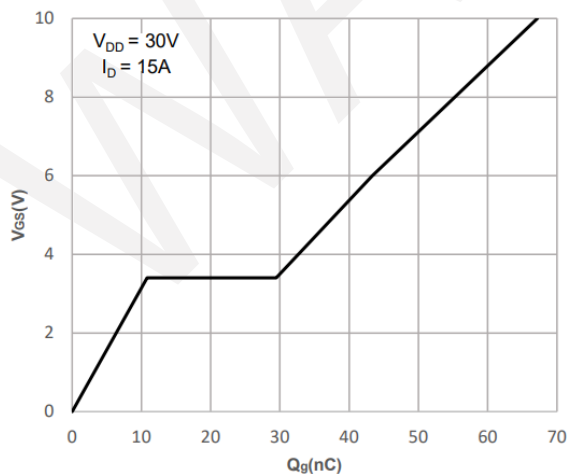
Typical Transfer Characteristics



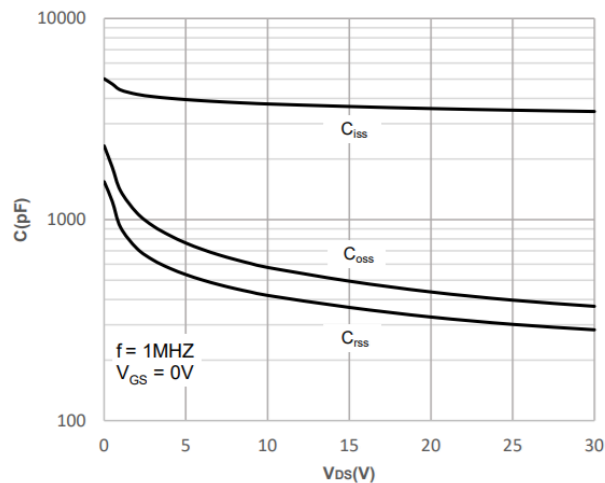
On-resistance vs. Drain Current



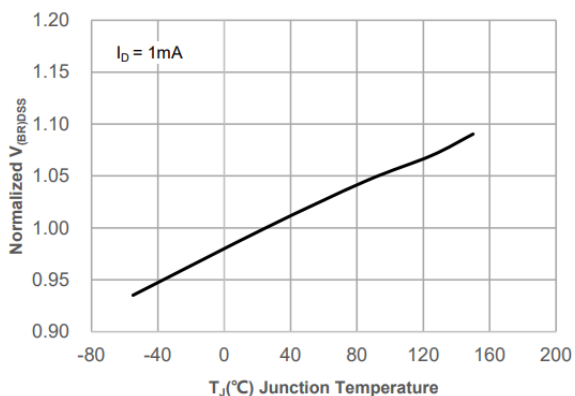
Body Diode Characteristics



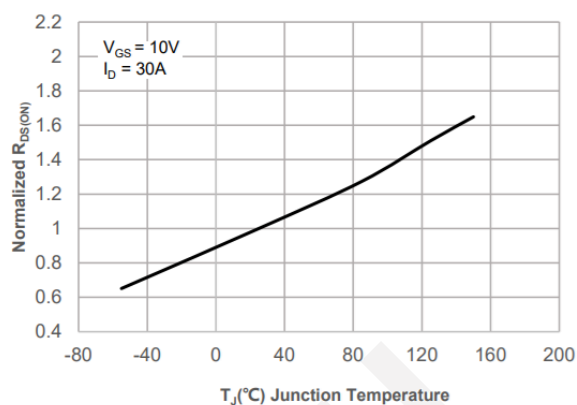
Gate Charge Characteristics



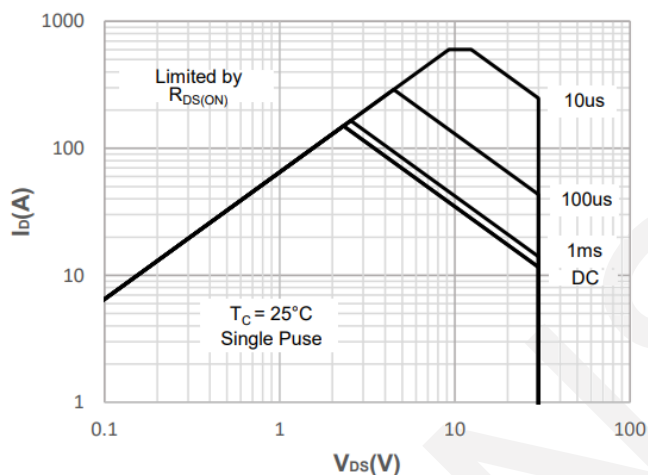
Capacitance Characteristics



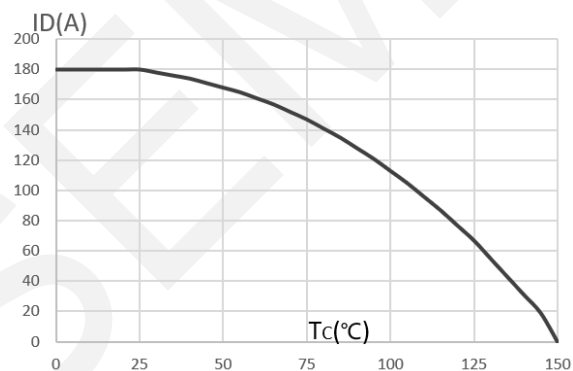
Normalized Breakdown Voltage vs.
Junction Temperature



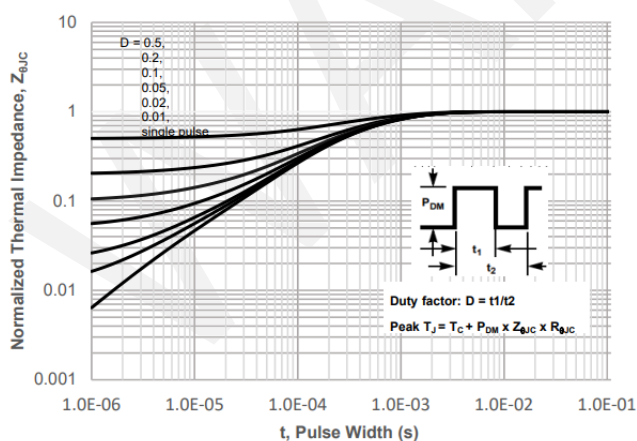
Normalized on Resistance vs.
Junction Temperature



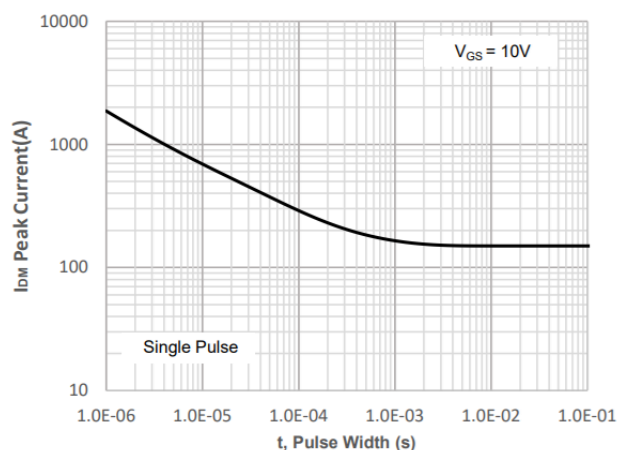
Maximum Safe Operating Area



Maximum Continuous Drain Current vs.
Case Temperature

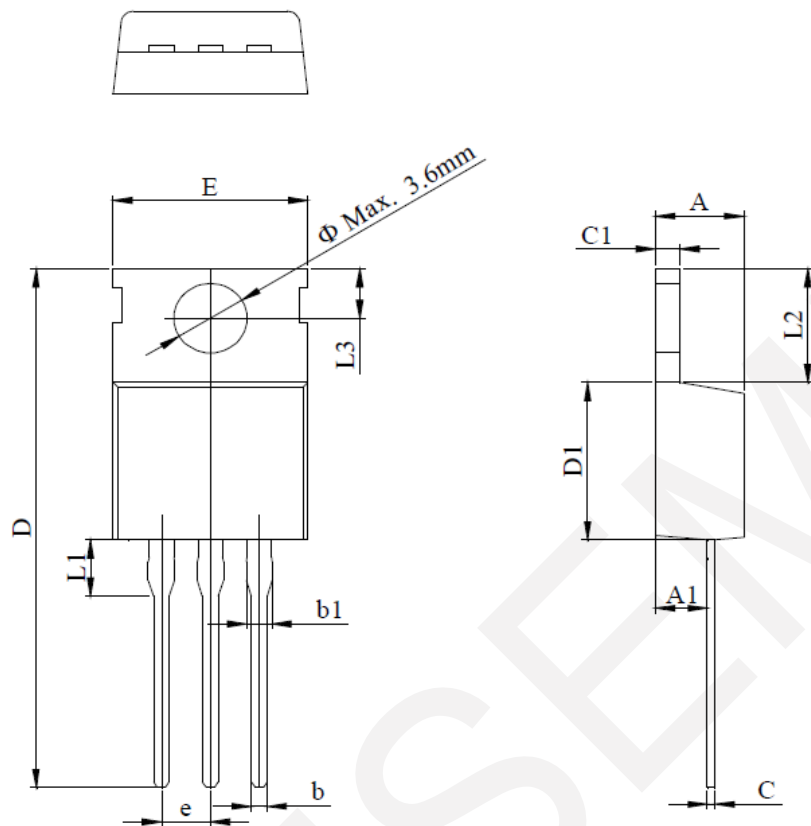


Normalized Maximum Transient
Thermal Impedance



Peak Current Capacity

8.Package Dimensions



DIM.	MILLIMETER		
	MIN.	NOM.	MAX.
A	4.24		4.70
A1	2.20		3.00
b	0.70		0.95
b1	1.14		1.70
C	0.40		0.60
C1	1.15		1.40
D	28.00		29.80
D1	8.80		9.90
E	9.70		10.50
L1			3.80
L2	6.25		6.90
L3	2.40		3.00
e		2.54 BSC	

9. Important Notice

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